

### INCHANGE SEMICONDUCTOR

## isc N-Channel Mosfet Transistor

## BUZ63

#### FEATURES

- 5.9A, 400V
- SOA is Power Dissipation Limited
- Nanosecond Switching Speeds
- Linear Transfer Characteristics
- High Input Impedance
- Majority Carrier Device
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- DESCRITION

Designed for applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power.

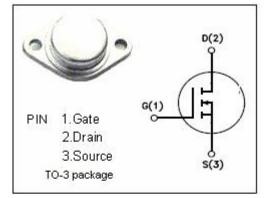
SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	400	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
ID	Drain Current-continuous@ TC=25°C	5.9	А
I <sub>DM</sub>	Drain Current-Single Plused	23	А
P <sub>tot</sub>	Total Dissipation@TC=25°C	78	W
Tj	Max. Operating Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

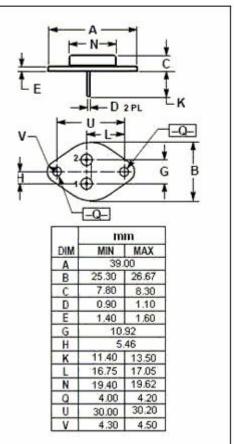
### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth j-c	Thermal Resistance, Junction to Case	1.6	°C/W
R <sub>th j-a</sub>	R <sub>th j-a</sub> Thermal Resistance, Junction to Ambient		°C/W

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#### isc website: www.iscsemi.com



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## ELECTRICAL CHARACTERISTICS

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =0.25mA	400			V
$V_{GS(th)}$	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.1		4.0	V
$V_{\text{SD}}$	Diode Forward On-voltage	I <sub>S</sub> = 11.8A ;V <sub>GS</sub> = 0			1.65	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 2.5A			1.0	Ω
Igss	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =400V; V <sub>GS</sub> = 0			250	μA
Gfs	Forward Transconductance	V <sub>DS</sub> = 25V; I <sub>D</sub> =2.5A	1.7			S
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =10V;			45	
tr	Rise Time	I <sub>D</sub> =2.7A;			60	20
$t_{d(off)}$	Turn-off Delay Time	ປ <sub>DD</sub> =30V; R <sub>GS</sub> =50 Ω			140	ns
t <sub>f</sub>	Fall Time				65	

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